

AMENDMENTS TO THE CLAIMS:

1. (Currently Amended) A thin film transistor comprising:
- an insulator substrate;
- a gate electrode located on the insulator substrate;
- a gate insulator film provided above the insulator substrate and the gate electrode; and
- a polycrystalline silicon film located on the gate insulator film, the gate electrode having a first center portion with a flat surface and a first pair of tapered end portions with inclined surfaces, an angle between each of the inclined surfaces of the first pair of tapered end portions and a surface of the insulator substrate being set within a range of $\pm 0^\circ 5'$ to 40° so that a uniform grain size of the polycrystalline silicon film is acquired above the first center portion and the first pair of tapered end portions, a gate withstand voltage of the thin film transistor is secured, and the inclined surfaces of the first pair of tapered end portions are prevented from increasing;
- a supplemental capacitor electrode located on the insulator substrate;
- a dielectric film located on the supplemental capacitor electrode and being formed integral with the gate insulator film; and
- a storage electrode defined in the polycrystalline silicon film on the dielectric film, the supplemental capacitor electrode having a second center portion with a flat surface and a second pair of tapered end portions with inclined surfaces, [an angle between each of the inclined surfaces of the second pair of tapered end portions and the surface of the insulator substrate being set within a range of 5° to 40°].